MOSFET – Power, Single N-Channel 60 V, 2.4 mΩ, 150 A

Features

- Small Footprint (5x6 mm) for Compact Design
- Low R_{DS(on)} to Minimize Conduction Losses
- Low Q_G and Capacitance to Minimize Driver Losses
- NVMFS5C628NLWF Wettable Flank Option for Enhanced Optical Inspection
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

	(1) = 20 (
Parameter			Symbol	Value	Unit	
Drain-to-Source Voltage			V _{DSS}	60	V	
Gate-to-Source Voltage			V _{GS}	±20	V	
Continuous Drain		$T_{C} = 25^{\circ}C$	I _D	150	А	
Current R _{θJC} (Notes 1, 3)	Steady	T _C = 100°C		110		
Power Dissipation	State	T _C = 25°C	PD	110	W	
R _{θJC} (Note 1)		$T_{\rm C} = 100^{\circ}{\rm C}$		56		
Continuous Drain	Steady	$T_A = 25^{\circ}C$	۱ _D	28	А	
Current R _{θJA} (Notes 1, 2, 3)		T _A = 100°C		20	1	
Power Dissipation	State	T _A = 25°C	PD	3.7	W	
R _{θJA} (Notes 1 & 2)		T _A = 100°C		1.9	1	
Pulsed Drain Current	$T_A = 25^{\circ}C, t_p = 10 \ \mu s$		I _{DM}	900	А	
Operating Junction and Storage Temperature		T _J , T _{stg}	–55 to + 175	°C		
Source Current (Body Diode)		I _S	120	А		
Single Pulse Drain-to-Source Avalanche Energy ($I_{L(pk)} = 9 A$)		E _{AS}	565	mJ		
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		ΤL	260	°C		

MAXIMUM RATINGS (T₁ = 25°C unless otherwise noted)

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case - Steady State	$R_{\theta JC}$	1.3	°C/W
Junction-to-Ambient - Steady State (Note 2)	$R_{\theta JA}$	40	

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.

2. Surface-mounted on FR4 board using a 650 mm², 2 oz. Cu pad.

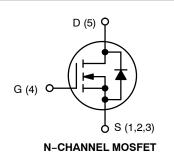
3. Maximum current for pulses as long as 1 second is higher but is dependent on pulse duration and duty cycle.

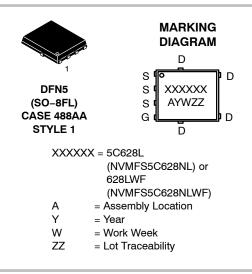


ON Semiconductor®

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V _{(BR)DSS}	R _{DS(ON)} MAX	I _D MAX
60 V	2.4 mΩ @ 10 V	150 A
00 V	3.3 mΩ @ 4.5 V	130 A





ORDERING INFORMATION

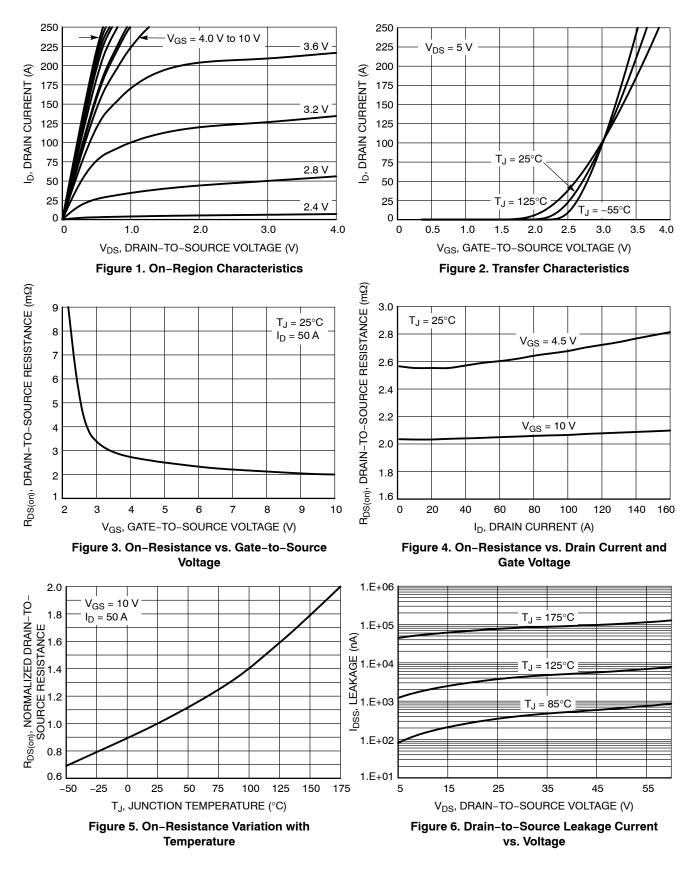
See detailed ordering, marking and shipping information in the package dimensions section on page 5 of this data sheet.

ELECTRICAL CHARACTERISTICS (T_J = $25^{\circ}C$ unless otherwise specified)

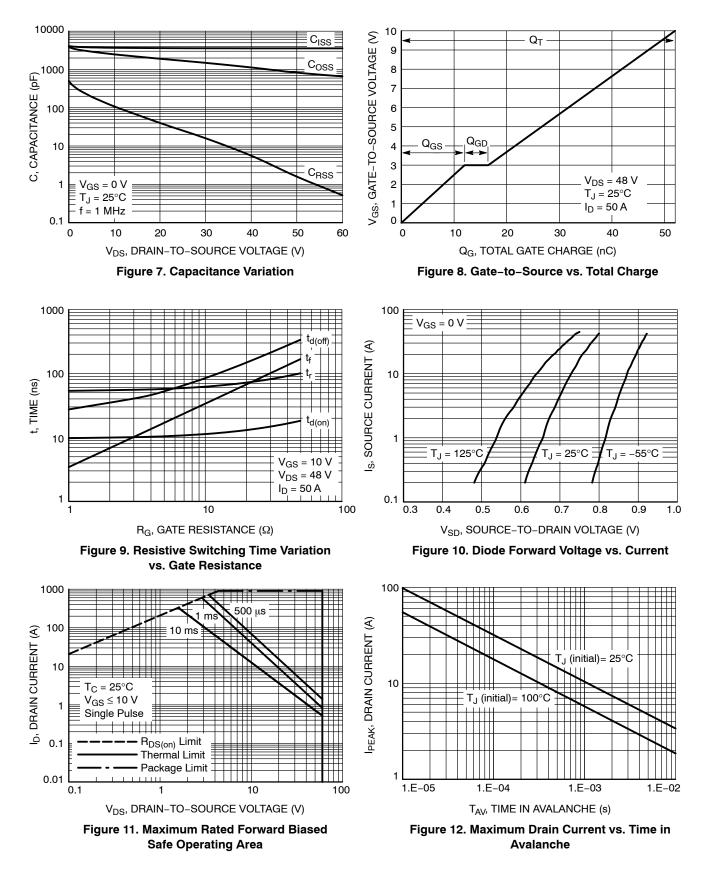
Parameter	Symbol	Test Condition		Min	Тур	Max	Unit	
OFF CHARACTERISTICS					<u> </u>			
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA		60			V	
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} / T _J				26		mV/°C	
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V,	T _J = 25 °C			10		
		V _{DS} = 60 V	T _J = 125°C			250	μA	
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _G	_S = 20 V			100	nA	
ON CHARACTERISTICS (Note 4)	1							
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 135 μA		1.2		2.0	V	
Threshold Temperature Coefficient	V _{GS(TH)} /T _J				-5.0		mV/°C	
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 10 V	I _D = 50 A		2.0	2.4		
		V _{GS} = 4.5 V	I _D = 50 A		2.6	3.3	mΩ	
Forward Transconductance	9 FS	V _{DS} =15 V, I _D = 50 A			110		S	
CHARGES AND CAPACITANCES								
Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 1 MHz, V _{DS} = 25 V			3600		pF	
Output Capacitance	C _{OSS}				1700			
Reverse Transfer Capacitance	C _{RSS}				28			
Total Gate Charge	Q _{G(TOT)}	V_{GS} = 4.5 V, V_{DS} = 48 V; I_{D} = 50 A			24		nC	
Total Gate Charge	Q _{G(TOT)}	V_{GS} = 10 V, V_{DS} = 48 V; I_{D} = 50 A			52		nC	
Threshold Gate Charge	Q _{G(TH)}	V _{GS} = 10 V, V _{DS} = 48 V; I _D = 50 A			6.0		nC V	
Gate-to-Source Charge	Q _{GS}				12			
Gate-to-Drain Charge	Q _{GD}				4.5			
Plateau Voltage	V _{GP}				3.0			
SWITCHING CHARACTERISTICS (Note 5)							
Turn-On Delay Time	t _{d(ON)}	V_{GS} = 10 V, V_{DS} = 48 V, I _D = 50 A, R _G = 2.5 Ω			10			
Rise Time	tr				55		ns	
Turn-Off Delay Time	t _{d(OFF)}				37			
Fall Time	t _f				8.5			
DRAIN-SOURCE DIODE CHARACTERIS	TICS							
Forward Diode Voltage	V_{SD} $V_{GS} = 0 V,$		$T_J = 25^{\circ}C$		0.8	1.2		
			T _J = 125°C		0.75		V	
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, dls/dt = 100 A/μs, I _S = 50 A			55			
Charge Time	t _a				28		ns	
Discharge Time	t _b				28			
Reverse Recovery Charge	Q _{RR}				60		nC	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 4. Pulse Test: pulse width $\leq 300 \ \mu$ s, duty cycle $\leq 2\%$. 5. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS



TYPICAL CHARACTERISTICS

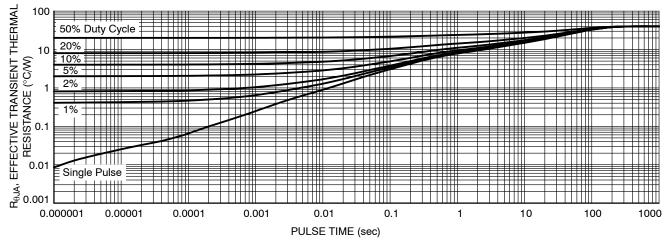


Figure 13. Thermal Characteristics

Device	Marking	Package	Shipping [†] 1500 / Tape & Reel	
NVMFS5C628NLT1G	5C628L	DFN5 (Pb-Free)		
NVMFS5C628NLWFT1G	628LWF	DFN5 (Pb-Free, Wettable Flanks)	1500 / Tape & Reel	
NVMFS5C628NLT3G	5C628L	DFN5 (Pb-Free)	5000 / Tape & Reel	
NVMFS5C628NLWFT3G	628LWF	DFN5 (Pb-Free, Wettable Flanks)	5000 / Tape & Reel	
NVMFS5C628NLAFT1G	5C628L	DFN5 (Pb-Free)	1500 / Tape & Reel	
NVMFS5C628NLWFAFT1G	628LWF	DFN5 (Pb-Free, Wettable Flanks)	1500 / Tape & Reel	

DEVICE ORDERING INFORMATION

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.





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